# NSN 5961-01-256-8881

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# **Inclosure Material:**

Metal

**Overall Length:** 

1.252 inches

# **Overall Height:**

0.340 inches

# **Overall Width:**

0.700 inches

# Mounting Facility Quantity:

2

# Internal Configuration:

Junction contact

# Joint Electronic Device Engineering Council/jedec/case Outline Designation:

# To-66

Electrode Internally-electrically Connected To Case:

Collector

# Mounting Method:

Unthreaded hole

# **Features Provided:**

Hermetically sealed case

# Criticality Code Justification:

Feat

# Semiconductor Material:

Silicon

# Voltage Rating In Volts Per Characteristic:

160.0 collector to base voltage/static/emitter open and 140.0 collector to emitter voltage/static/base open and 7.0 emitter to base voltage, static, collector open

# **Current Rating Per Characteristic:**

3.00 amperes source cutoff current and 2.00 amperes source cutoff current

#### **Power Rating Per Characteristic:**

5.8 watts small-signal input power, common-collector absolute

# Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

#### **Special Features:**

Item must comply with requirements of defense electronics supply center production standard no. L03745; for navy nuclear propulsion plant products only; junction pattern arrangement: npn

# **Terminal Type And Quantity:**

2 pin and 1 case

Shelf Life:

N/a

#### Unit Of Measure:

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Demilitarization:

No

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